

HiPerRF™

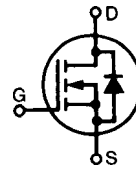
Power MOSFETs

F-Class: MegaHertz Switching

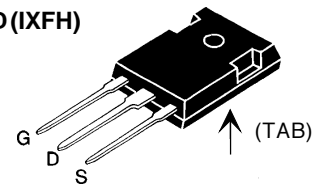
N-Channel Enhancement Mode
 Avalanche Rated, Low Q_g , Low Intrinsic R_g
 High dV/dt , Low t_{rr}

IXFH 28N50F
 IXFT 28N50F

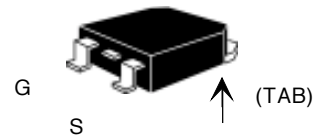
$V_{DSS} = 500V$
 $I_{D25} = 28A$
 $R_{DS(on)} = 190m\Omega$
 $t_{rr} \leq 250 ns$



TO-247 AD (IXFH)



TO-268 (IXFT) Case Style



G = Gate, D = Drain,
 S = Source, TAB = Drain

Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ C$ to $150^\circ C$	500	V
V_{DGR}	$T_J = 25^\circ C$ to $150^\circ C$; $R_{GS} = 1 M\Omega$	500	V
V_{GS}	Continuous	± 20	V
V_{GSM}	Transient	± 30	V
I_{D25}	$T_C = 25^\circ C$	28	A
I_{DM}	$T_C = 25^\circ C$, pulse width limited by T_{JM}	112	A
I_{AR}	$T_C = 25^\circ C$	28	A
E_{AR}	$T_C = 25^\circ C$	35	mJ
E_{AS}	$T_C = 25^\circ C$	1.5	J
dv/dt	$I_S \leq I_{DM}$, $di/dt \leq 100 A/\mu s$, $V_{DD} \leq V_{DSS}$ $T_J \leq 150^\circ C$, $R_G = 2 \Omega$	10	V/ns
P_D	$T_C = 25^\circ C$	315	W
T_J		-55 ... +150	$^\circ C$
T_{JM}		150	$^\circ C$
T_{stg}		-55 ... +150	$^\circ C$
T_L	1.6 mm (0.063 in.) from case for 10 s	300	$^\circ C$
M_d	Mounting torque	TO-247	1.13/10 Nm/lb.in.
Weight		TO-247	6 g
		TO-268	4 g

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ C$, unless otherwise specified)		
		min.	typ.	max.
V_{DSS}	$V_{GS} = 0 V$, $I_D = 1 mA$	500		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 4 mA$	2.0		4.0 V
I_{GSS}	$V_{GS} = \pm 20 V$, $V_{DS} = 0$			$\pm 100 nA$
I_{DSS}	$V_{DS} = V_{DSS}$ $V_{GS} = 0 V$ $T_J = 125^\circ C$			50 μA 1.5 mA
$R_{DS(on)}$	$V_{GS} = 10 V$, $I_D = 0.5 I_{D25}$ Note 1			190 m Ω

Features

- RF capable MOSFETs
- Double metal process for low gate resistance
- Unclamped Inductive Switching (UIS) rated
- Low package inductance - easy to drive and to protect
- Fast intrinsic rectifier

Applications

- DC-DC converters
- Switched-mode and resonant-mode power supplies, >500kHz switching
- DC choppers
- 13.5 MHz industrial applications
- Pulse generation
- Laser drivers
- RF amplifiers

Advantages

- Space savings
- High power density

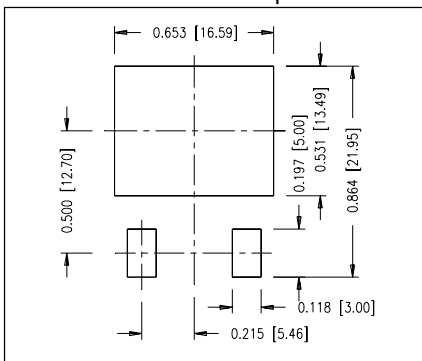
Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
g_{fs}	$V_{DS} = 10\text{ V}; I_D = 0.5 I_{D25}$ Note 1	12	18	S
C_{iss}	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$		3000	pF
C_{oss}			500	pF
C_{rss}			130	pF
$t_{d(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 V_{DSS}, I_D = 0.5 I_{D25}$ $R_G = 2.0\ \Omega$ (External)		15	ns
t_r			13	ns
$t_{d(off)}$			41	ns
t_f			8	ns
$Q_{g(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 V_{DSS}, I_D = 0.5 I_{D25}$		95	nC
Q_{gs}			20	nC
Q_{gd}			38	nC
R_{thJC}			0.39	K/W
R_{thCK}	(TO-247)		0.25	K/W

Source-Drain Diode

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
I_S	$V_{GS} = 0\text{ V}$			28 A
I_{SM}	Repetitive; pulse width limited by T_{JM}			112 A
V_{SD}	$I_F = I_S, V_{GS} = 0\text{ V}$, Note 1			1.5 V
t_{rr}	$I_F = I_S, -di/dt = 100\text{ A}/\mu\text{s}, V_R = 100\text{ V}$			250 ns
Q_{RM}			1.0	μC
I_{RM}			12	A

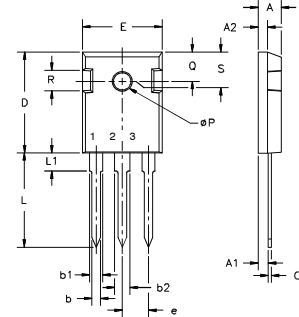
Note: 1. Pulse test, $t \leq 300\ \mu\text{s}$, duty cycle $d \leq 2\%$

Min Recommended Footprint



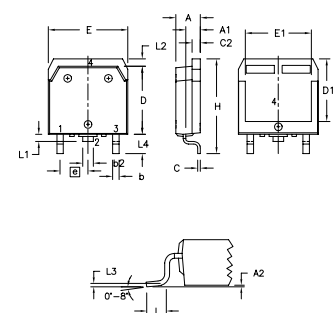
IXYS reserves the right to change limits, test conditions, and dimensions.

TO-247 AD Outline



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.7	5.3	.185	.209
A ₁	2.2	2.54	.087	.102
A ₂	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b ₁	1.65	2.13	.065	.084
b ₂	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L1		4.50		.177
ØP	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15	BSC	.242	BSC

TO-268 Outline



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.9	5.1	.193	.201
A ₁	2.7	2.9	.106	.114
A ₂	.02	.25	.001	.010
b	1.15	1.45	.045	.057
b ₂	1.9	2.1	.75	.83
C	.4	.65	.016	.026
D	13.80	14.00	.543	.551
E	15.85	16.05	.624	.632
E ₁	13.3	13.6	.524	.535
e	5.45	BSC	.215	BSC
H	18.70	19.10	.736	.752
L	2.40	2.70	.094	.106
L1	1.20	1.40	.047	.055
L2	1.00	1.15	.039	.045
L3	0.25	BSC	.010	BSC
L4	3.80	4.10	.150	.161